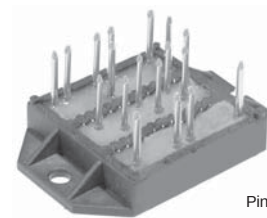
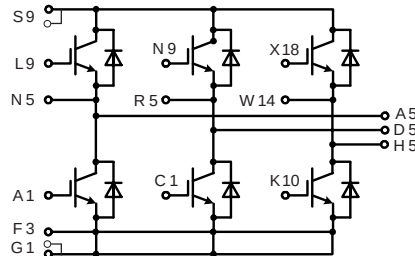


IGBT Module

Sixpack in ECO-PAC 2

$$\begin{aligned} I_{C25} &= 31 \text{ A} \\ V_{CES} &= 600 \text{ V} \\ V_{CE(sat) \text{ typ.}} &= 1.9 \text{ V} \end{aligned}$$



Pin arrangement see outlines

IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	31	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	21	A
I_{CM}	$V_{GE} = \pm 15 \text{ V}; R_G = 47 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	40	A
V_{CEK}		V_{CES}	
t_{SC} (SCSOA)	$V_{CE} = 600 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 47 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	100	W

Features

- NPT IGBT's
 - positive temperature coefficient of saturation voltage
 - fast switching
- FRED diodes
 - fast reverse recovery
 - low forward voltage
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated DCB ceramic base plate

Typical Applications

- AC drives
- power supplies with power factor correction

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 20 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.9 2.2	V V
$V_{GE(th)}$	$I_C = 0.5 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.7	0.6 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			100 nA
$t_{d(on)}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 10 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 82 \Omega$		50	ns
t_r			55	ns
$t_{d(off)}$			300	ns
t_f			30	ns
E_{on}			0.9	mJ
E_{off}			0.7	mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		1100	pF
Q_{Gon}	$V_{CE} = 300 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 20 \text{ A}$		65	nC
R_{thJC}	(per IGBT)			1.3 K/W
R_{thJH}	with heatsink compound (0.42 K/m.K; 50 μm)		2.5	K/W

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IXYS Semiconductor GmbH
Edisonstr. 15, D-68623 Lampertheim
Phone: +49-6206-503-0, Fax: +49-6206-503627

www.ixys.net

IXYS Corporation
3540 Bassett Street, Santa Clara CA 95054
Phone: (408) 982-0700, Fax: 408-496-0670

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	35	A
I_{F80}	$T_C = 80^\circ\text{C}$	22	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 20\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.9 1.4	2.1 V
I_{RM} t_{rr}	$I_F = 15\text{ A}; di_F/dt = -400\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$		13 90	A ns
R_{thJC} R_{thJH}	with heatsink compound (0.42 K/m.K; 50 μm)		4.6	2.3 K/W K/W

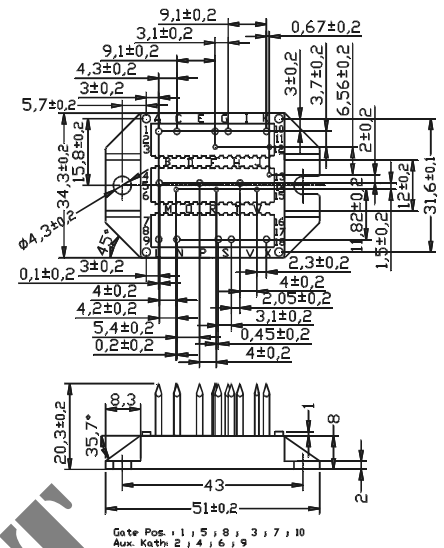
Data according to IEC 60747 and refer to a single diode unless otherwise stated.

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}; t = 1\text{ s}$	3600	V~
M_d	mounting torque (M4)	1.5 - 2.0 14 - 18	Nm lb.in.
a	Max. allowable acceleration	50	m/s^2

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_s	Creepage distance on surface (Pin to heatsink)	11.2		mm
d_A	Strike distance in air (Pin to heatsink)	11.2		mm
Weight		24		g

Dimensions in mm (1 mm = 0.0394")

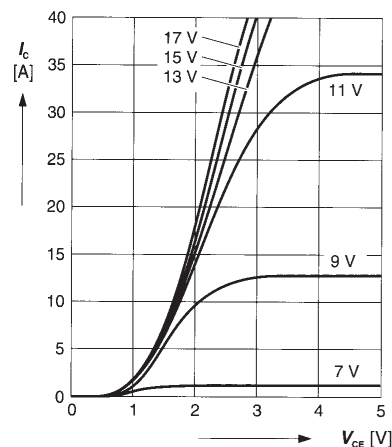


IGBT

Typ. output characteristics

$$I_C = f(V_{CE})$$

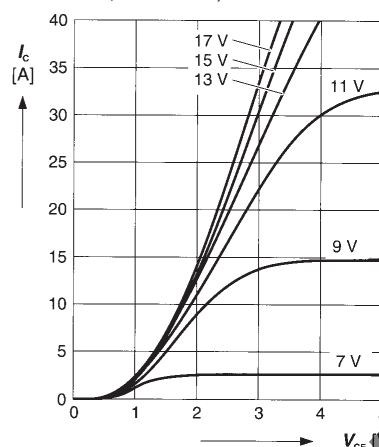
parameter: $t_p = 250 \mu s$; $T_j = 25^\circ C$



Typ. output characteristics

$$I_C = f(V_{CE})$$

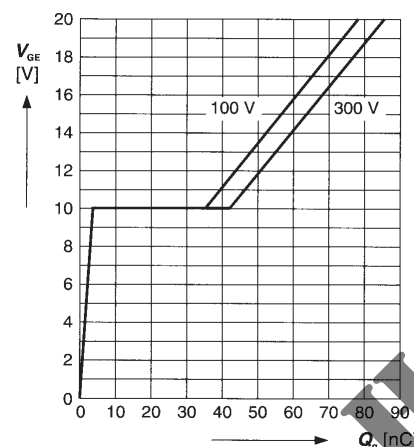
parameter: $t_p = 250 \mu s$; $T_j = 125^\circ C$



Typ. gate charge

$$V_{GE} = f(Q_g)$$

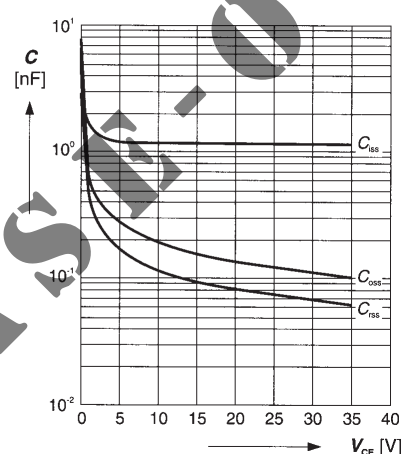
parameter: $I_{C,puls} = 20 A$



Typ. capacitances

$$C = f(V_{CE})$$

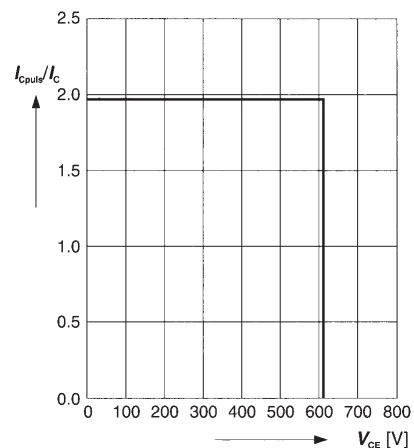
parameter: $V_{GE} = 0 V$; $f = 1 MHz$



Reverse biased safe operating area

$$I_{C,puls} = f(V_{CE}), T_j = 150^\circ C$$

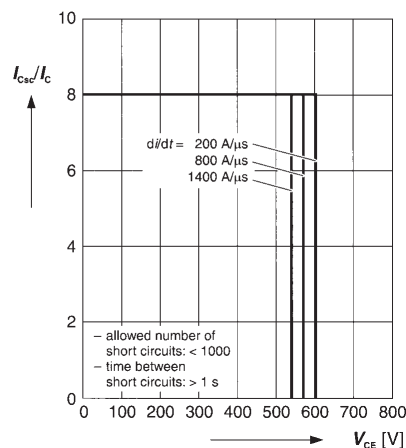
parameter: $V_{GE} = 15 V$



Short circuit safe operating area

$$I_{C,sc} = f(V_{CE}), T_j = 150^\circ C$$

parameter: $V_{GE} = \pm 15 V$; $t_{sc} \leq 10 \mu s$; $L < 50 nH$

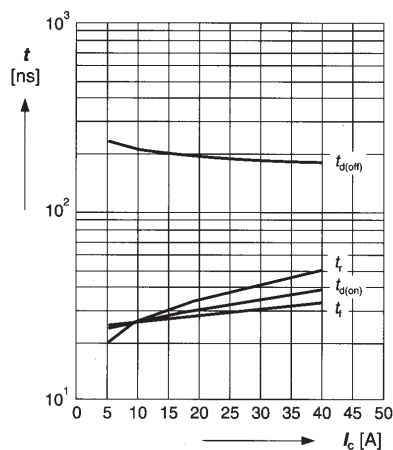


IGBT

Typ. switching time

$t = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$

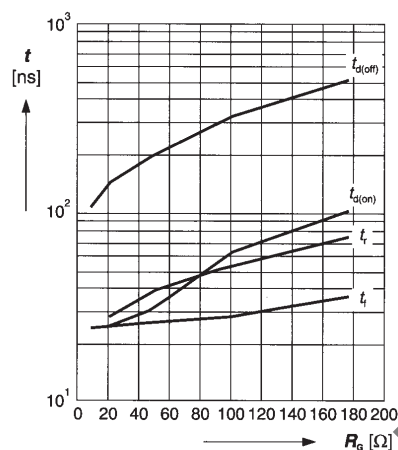
parameter: $V_{CE} = 300\text{ V}$; $V_{GE} = \pm 15\text{ V}$; $R_G = 47\ \Omega$



Typ. switching time

$t = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$

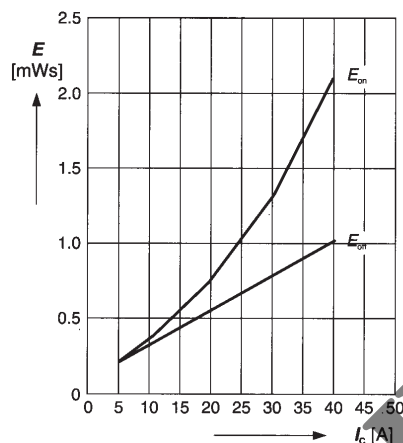
parameter: $V_{CE} = 300\text{ V}$; $V_{GE} = \pm 15\text{ V}$; $I_C = 20\text{ A}$



Typ. switching losses

$E = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$

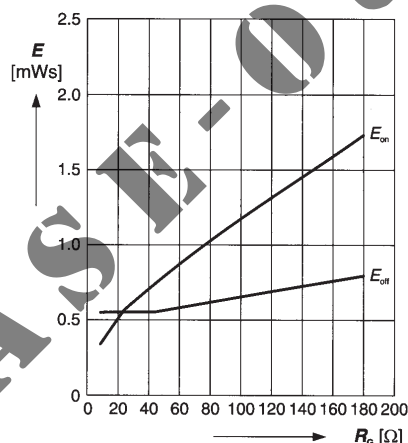
parameter: $V_{CE} = 300\text{ V}$; $V_{GE} = \pm 15\text{ V}$; $R_G = 47\ \Omega$



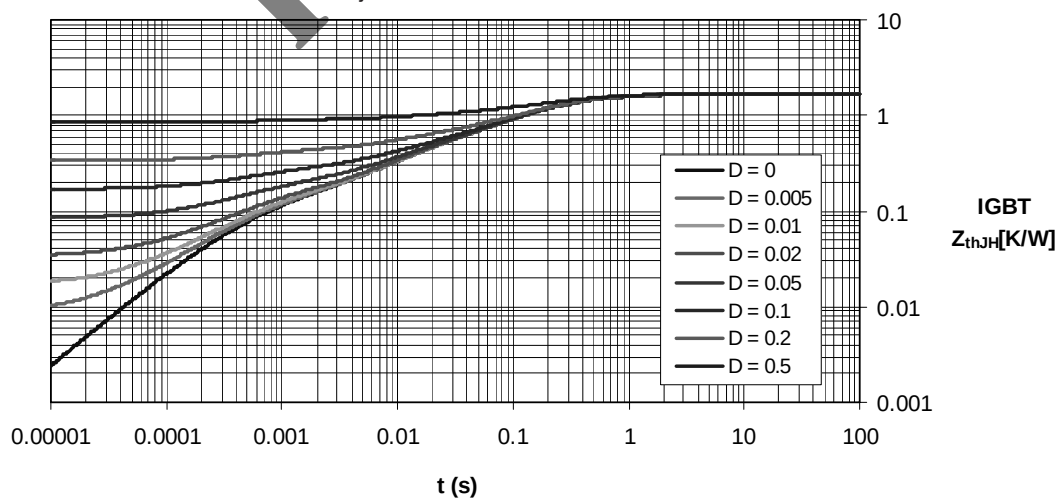
Typ. switching losses

$E = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$

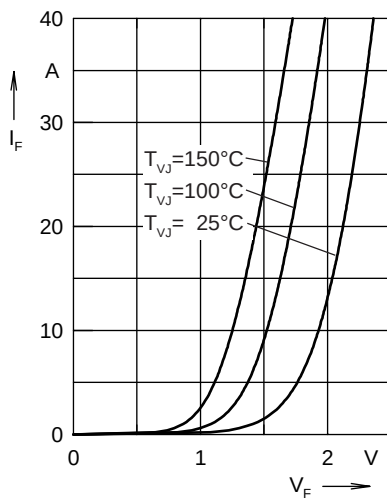
parameter: $V_{CE} = 300\text{ V}$; $V_{GE} = \pm 15\text{ V}$; $I_C = 20\text{ A}$



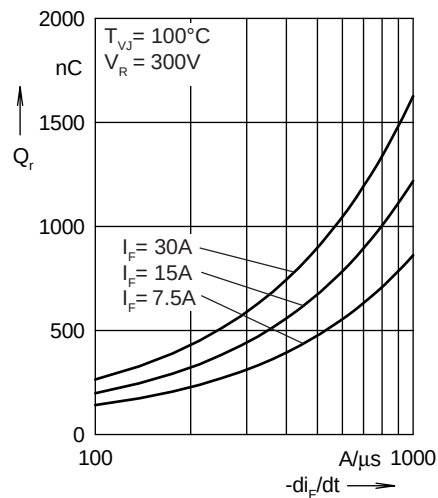
Transient thermal resistance junction to heatsink



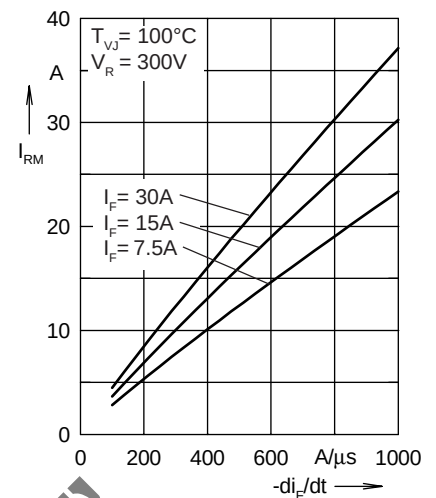
Diode



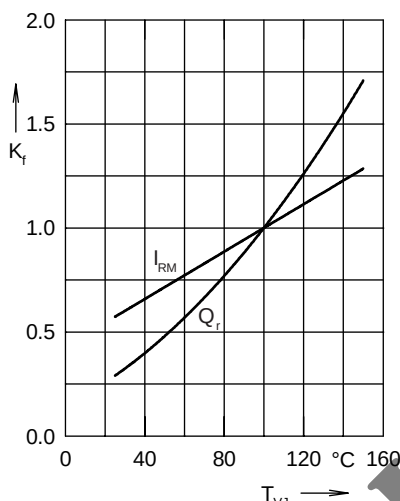
Forward current I_F versus V_F



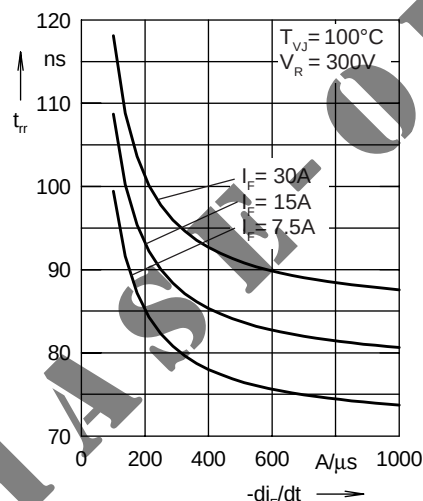
Reverse recovery charge Q_r versus $-di_F/dt$



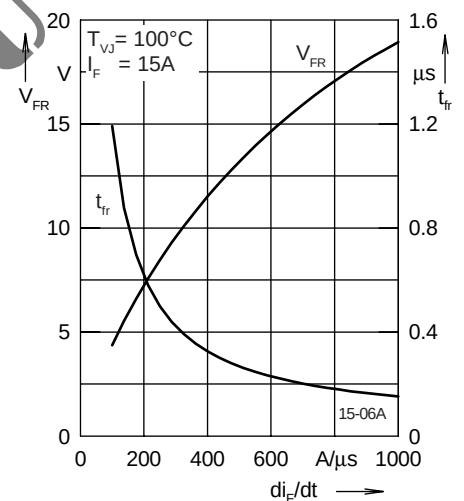
Peak reverse current I_{RM} versus $-di_F/dt$



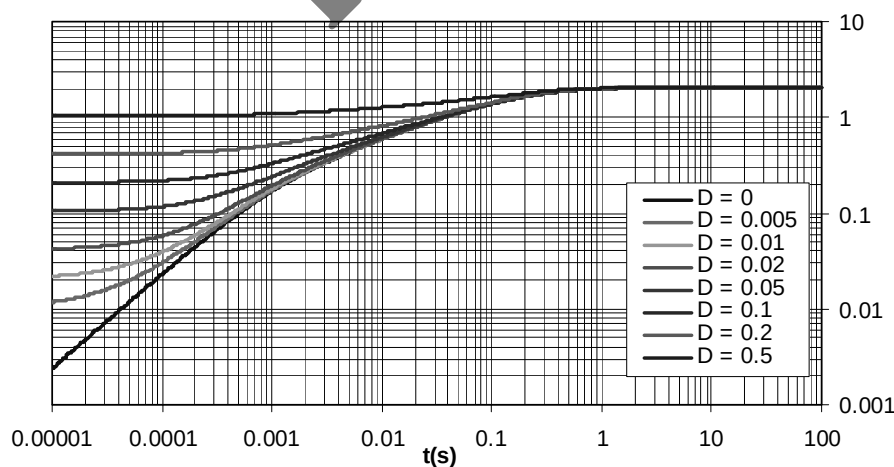
Dynamic parameters Q_r , I_{RM} versus T_{VJ}



Recovery time t_{rr} versus $-di_F/dt$



Peak forward voltage V_{FR} and t_{rr} versus di_F/dt



Transient thermal resistance junction to heatsink

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